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Altri autori (Persone)	HeniniMohamed
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DROPLET EPITAXY; 4.3 DROPLET DEPOSITION; 4.4 NANOSTRUCTURE FORMATION; 4.5 CAPPING AND POST-GROWTH ANNEALING PROCEDURES
4.6 PULSED DROPLET EPITAXYACKNOWLEDGEMENTS; REFERENCES; Chapter 5 - Migration-enhanced epitaxy for low-dimensional structures; 5.1 INTRODUCTION; 5.2 AREA SELECTIVE EPITAXY BY MEE; 5.3 POLAR DIAGRAM OF THE GROWTH RATE OF III-V COMPOUND SEMICONDUCTORS; 5.4 FORMATION OF CRYSTAL FACETS AT THE BOUNDARIES OF MICROSTRUCTURES; 5.5 AREA SELECTIVE GROWTH ON (001) GAAS SUBSTRATE BY MEE USING AS4 AND AS2; 5.6 AREA SELECTIVE GROWTH ON (111)B GAAS SUBSTRATE BY MEE; 5.7 SUMMARY; ACKNOWLEDGEMENTS; REFERENCES; Chapter 6 - MBE growth of high-mobility 2DEG; 6.1 INTRODUCTION; 6.2 HIGH-MOBILITY MBE SYSTEM
Chapter 10 - Effect of antimony coverage on InAs/GaAs (001) heteroepitaxy

Sommario/riassunto

This multi-contributor handbook discusses Molecular Beam Epitaxy (MBE), an epitaxial deposition technique which involves laying down layers of materials with atomic thicknesses on to substrates. It summarizes MBE research and application in epitaxial growth with close discussion and a 'how to' on processing molecular or atomic beams that occur on a surface of a heated crystalline substrate in a vacuum. MBE has expanded in importance over the past thirty years (in terms of unique authors, papers and conferences) from a pure research domain into commercial applications (prototype devi